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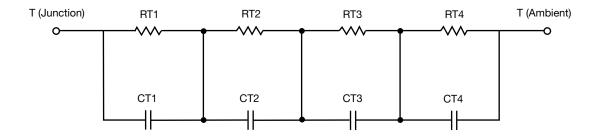
## **R-C Thermal Model Parameters**

#### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### R-C THERMAL MODEL FOR TANK CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RT1	N/A	204.6048m	N/A		
RT2	N/A	429.3522m	N/A		
RT3	N/A	390.7889m	N/A		
RT4	N/A	80.7150m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	3.7066m	N/A		
CT2	N/A	103.5817m	N/A		
CT3	N/A	108.7360m	N/A		
CT4	N/A	593.3694m	N/A		

#### Note

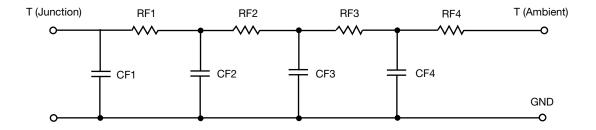
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	208.0792m	N/A		
RF2	N/A	491.5708m	N/A		
RF3	N/A	337.0360m	N/A		
RF4	N/A	70.9322m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	3.0975m	N/A		
CF2	N/A	35.8867m	N/A		
CF3	N/A	44.1610m	N/A		
CF4	N/A	45.8890m	N/A		

### Note

• n/a indicates not applicable





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